



Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
100V	70mΩ@10V	10A

Feature

- Split Gate Trench Technology
- Low $R_{DS(ON)}$
- Low Gate Charge
- Low Gate Resistance
- 100% UIS Tested

Application

- Power Switching Application

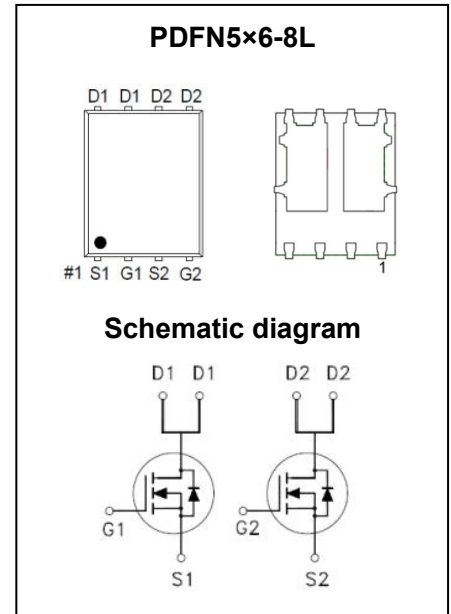
MARKING:



T850ND10L = Device Code

XX = Date Code

Solid Dot = Green Indicator



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit	
Drain - Source Voltage	V_{DS}	100	V	
Gate - Source Voltage	V_{GS}	±20	V	
Continuous Drain Current ¹	$T_C = 25^\circ\text{C}$	I_D	10	A
	$T_C = 100^\circ\text{C}$	I_D	7	A
Pulsed Drain Current ²	I_{DM}	40	A	
Power Dissipation ⁴	$T_C = 25^\circ\text{C}$	P_D	7.4	W
Thermal Resistance from Junction to Ambient ⁵	$R_{\theta JA}$	66	$^\circ\text{C/W}$	
Thermal Resistance from Junction to Case	$R_{\theta JC}$	17	$^\circ\text{C/W}$	
Junction Temperature	T_J	150	$^\circ\text{C}$	
Storage Temperature	T_{STG}	-55~ +150	$^\circ\text{C}$	

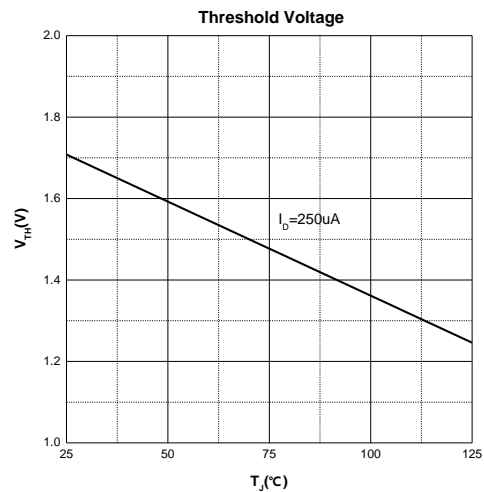
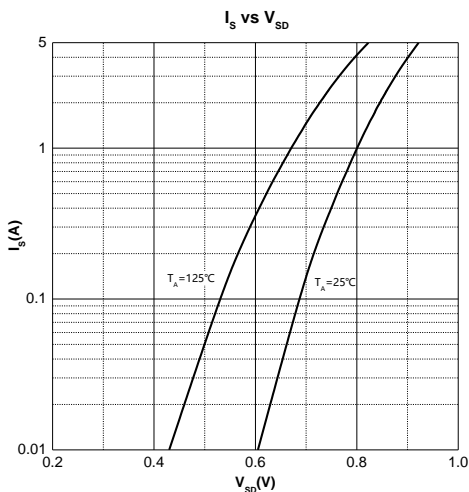
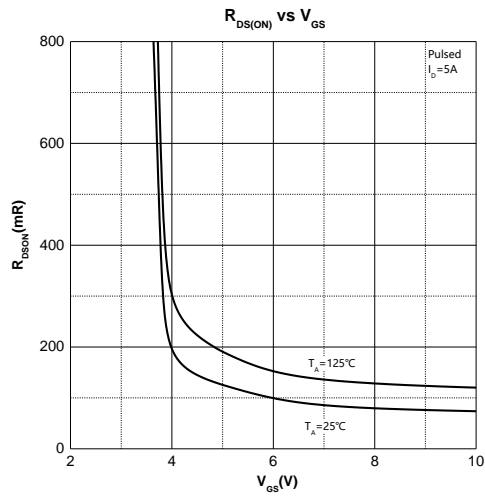
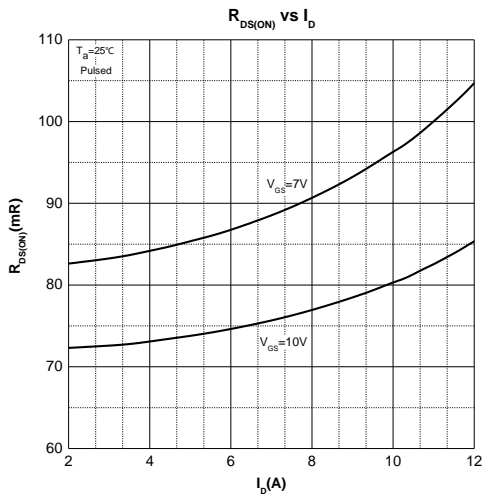
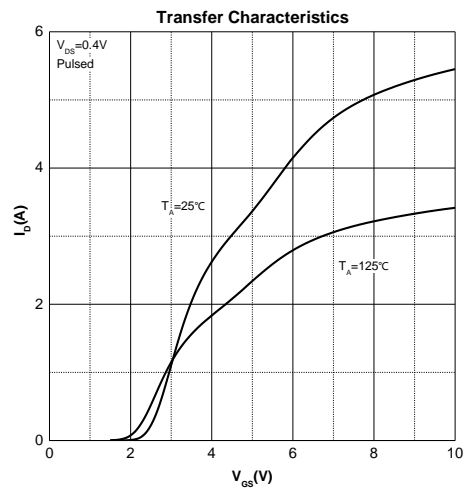
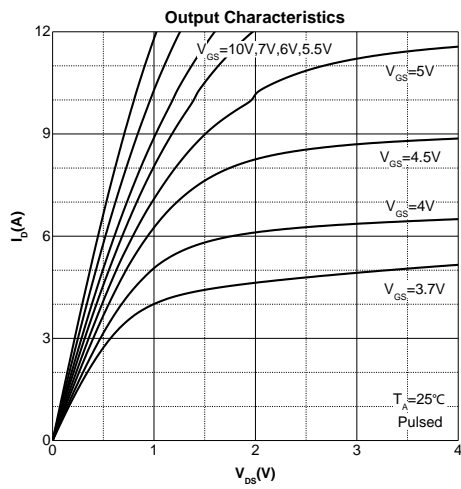
MOSFET ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain - Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	100			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 100V, V_{GS} = 0V$			1	μA
Gate - Body Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 100	nA
On Characteristics³						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.0	1.7	3.0	V
Drain-source On-resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 5A$		70	85	m Ω
Forward Transconductance	g_{FS}	$V_{DS} = 5V, I_D = 5A$		14		S
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS} = 50V, V_{GS} = 0V, f = 1MHz$		221		pF
Output Capacitance	C_{oss}			78		
Reverse Transfer Capacitance	C_{rss}			4.4		
Gate Resistance	R_g	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$		2.5		Ω
Switching Characteristics						
Total Gate Charge	Q_g	$V_{DS} = 50V, V_{GS} = 10V, I_D = 5A$		3		nC
Gate-source Charge	Q_{gs}			0.9		
Gate-drain Charge	Q_{gd}			1		
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 50V, V_{GS} = 10V, R_L = 10\Omega$ $R_G = 3\Omega$		5		ns
Turn-on Rise Time	t_r			3		
Turn-off Delay Time	$t_{d(off)}$			15		
Turn-off Fall Time	t_f			4		
Source - Drain Diode Characteristics						
Diode Forward Voltage ⁴	V_{SD}	$V_{GS} = 0V, I_S = 10A$			1.2	V
Diode Reverse Recovery Time	t_{rr}	$I_F = 5A, di/dt = 500A/ms$		15		ns
Diode Reverse Recovery Charge	Q_{rr}	$I_F = 5A, di/dt = 500A/ms$		44		nC

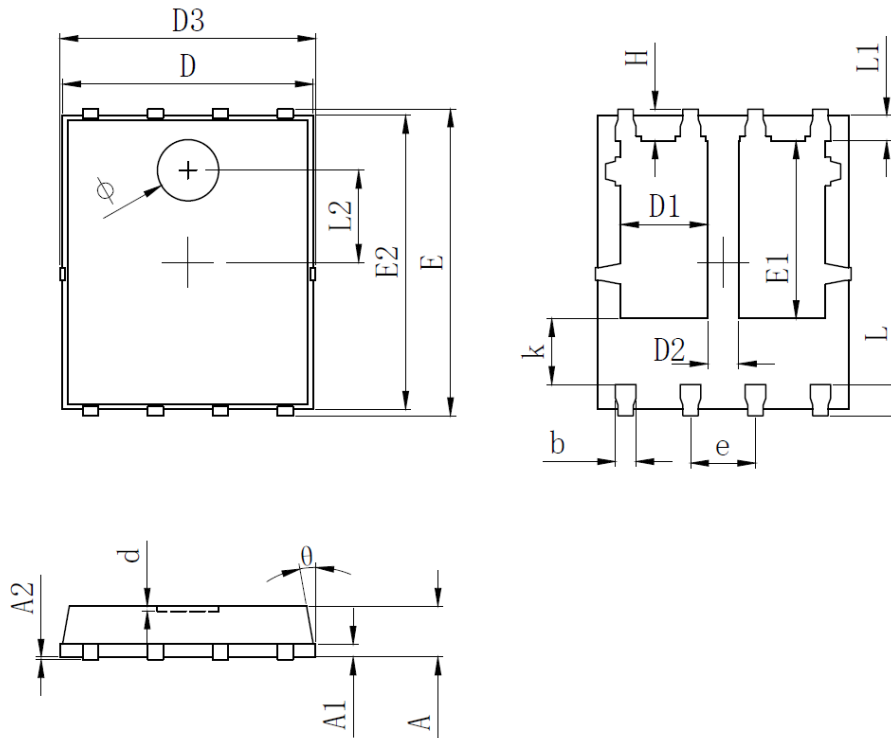
Notes :

- 1.The maximum current rating is limited by package.And device mounted on a large heatsink
- 2.Pulse Test : Pulse Width $\leq 10\mu s$, duty cycle $\leq 1\%$.
- 3.Pulse Test : Pulse Width $\leq 300\mu s$, duty cycle $\leq 2\%$.
- 4.The power dissipation P_D is limited by $T_{J(MAX)} = 150^\circ\text{C}$.And device mounted on a large heatsink
- 5.Device mounted on $1in^2$ FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$.

Typical Characteristics



PDFN5×6-8L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.100	0.035	0.043
A1	0.254REF		0.010REF	
A2	0.000	0.050	0.000	0.002
D	4.824	4.976	0.190	0.196
D1	1.605	1.805	0.063	0.071
D2	0.500	0.700	0.020	0.028
D3	4.924	5.076	0.194	0.200
E	5.924	6.076	0.233	0.239
E1	3.375	3.575	0.133	0.141
E2	5.674	5.826	0.223	0.229
b	0.350	0.450	0.014	0.018
e	1.270TYP		0.050TYP	
L	0.534	0.686	0.021	0.027
L1	0.424	0.576	0.017	0.023
L2	1.800REF		0.071REF	
k	1.190	1.390	0.047	0.055
H	0.549	0.701	0.022	0.028
θ	8°	12°	8°	12°
Φ	1.100	1.300	0.043	0.051
d	-	0.100	-	0.004